# Fiducial Mark requirements from the viewpoints of Actinic Blank Inspection tool for phase defect mitigation on EUVL Mask



#### Fabrication of FM

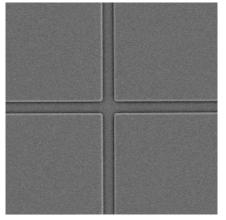
2 sets of FM matrix were fabricated by resist exposure by EB writer and ML etching process.

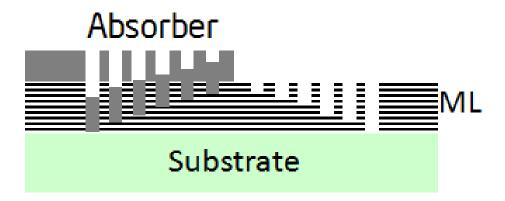
Line width:  $1, 3, 5, 7 \mu m$ 

Line depth: 65, 130, 180, 215, 290, 300 nm

Etching Layer: ML

- One set is covered by absorber, and other one is not.
  - 2 Masks were prepared. One is coated by 85 nm thickness absorber, and the other is by 50 nm thickness.
- Took data by AFM, SEM, EB writer, and ABI tool.

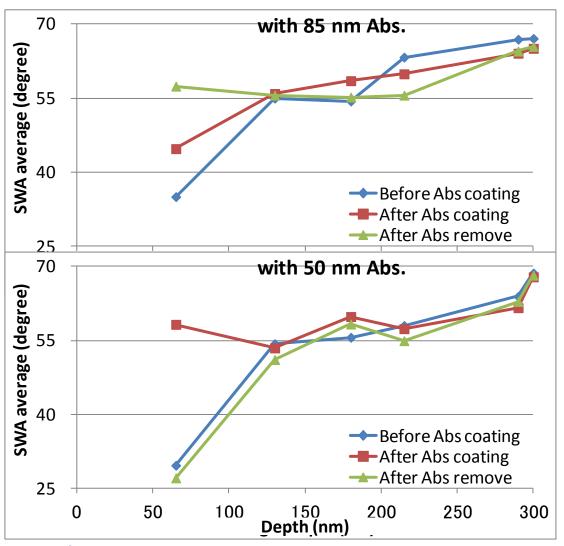






# AFM measurement summary SideWall Angle (SWA) average

Calculated from 4 data of same width target FMs



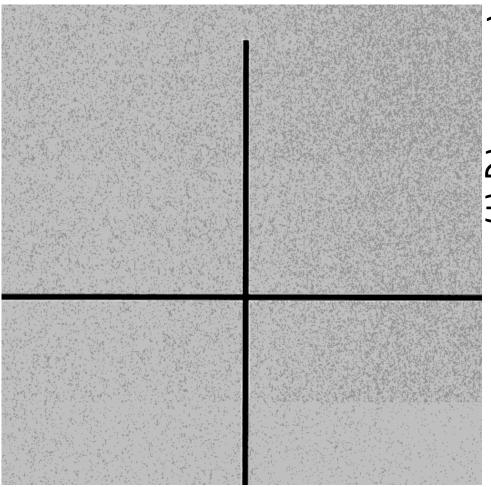
SWA of Shallower depth FMs varied by process.

Deeper ones' are relatively stable.

As SWA change may cause edge position shift, > 100 nm depth is proper.



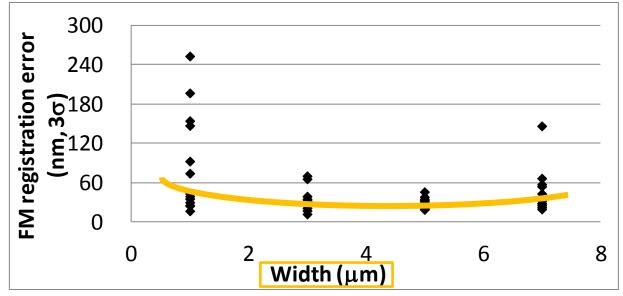
#### ABI Measurement & Center location calculation

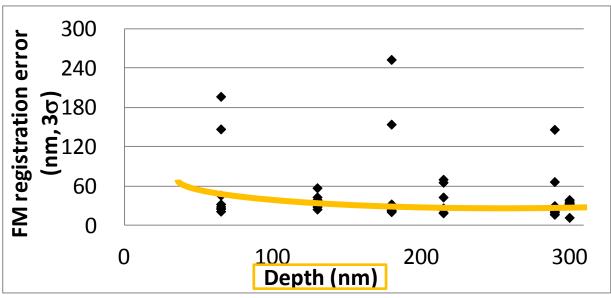


- Obtain position
   information of edge on
   V&H lines (total 128 points)
- 2. Compensate rotation
- 3. Calculate line center locations and their accuracy on V&H lines



## FM registration error (30) by ABI





Generally, deeper & wider FM is better. However, these results don't meet the proposed requirement.

(< 10 nm)

Need ABI's improvement of FM registration accuracy.



#### Summary

#### FM recommendations are:

- ✓ ML etched
- √ > 100 nm line depth
- ✓ 3-5 µm line width

ABI tool is required to equip Magnified Optics to achieve (MO) i.e. smaller pixel size on mask < 10 nm (30) error for mitigation (position & size).

We need <u>further optimization of FM for the MO of</u> LT ABI tool.



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# **Backup**



